



Rapid Single Cell Manufacturing of Thin-Film CIGS

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The XsunX Approach

❖ Combine:

- **CIGS Deposition Technology**, and
 - ✓ Best Thin Film Performance
- **Rapid Single Substrate Processing using Hard Drive (HD) Equipment**
 - ✓ Established a Joint Development Agreement with the Industrial Leader for HD Equipment → *Intevac*
 - Co-Located Technical Team, Deposition Systems, and Metrology Equipment
 - ✓ Production Volume Achieved Via Speed Rather Than Large Area Processing

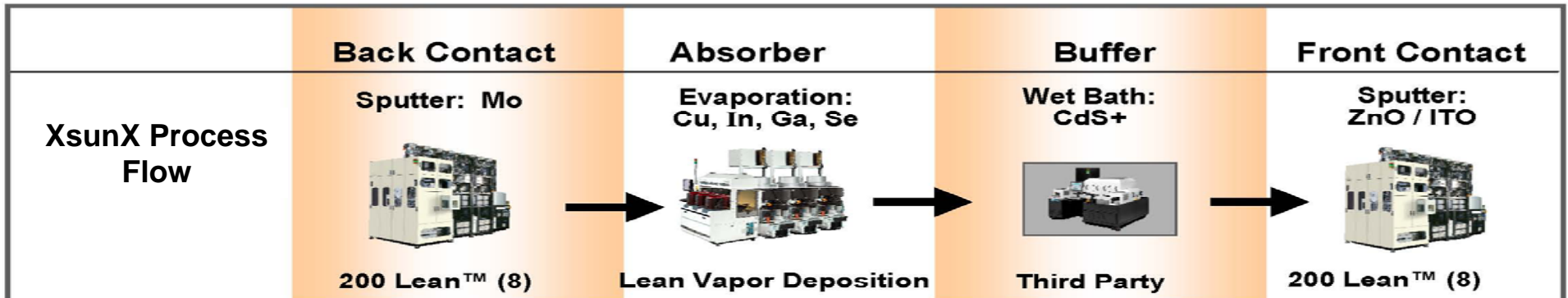
❖ Final Goal → High Volume Production of CIGS Cells that have a Similar Efficiency as Poly x-Si Produced at a Lower Cost

- **Module Uses Same Glass, Encapsulant (EVA, PVB), Dual Rated j-Box, and Frame as Current x-Si Modules → The Difference is a Lower Cost Cell**

Result : Equal Performance at a Lower Cost → Best \$/W



XsunX Combines Mature HDD Systems with CIGS Expertise



❖ Better Manufacturing Technology

- True Single Substrate Processing
- State-of-the-Art Control System

❖ Process Flexibility

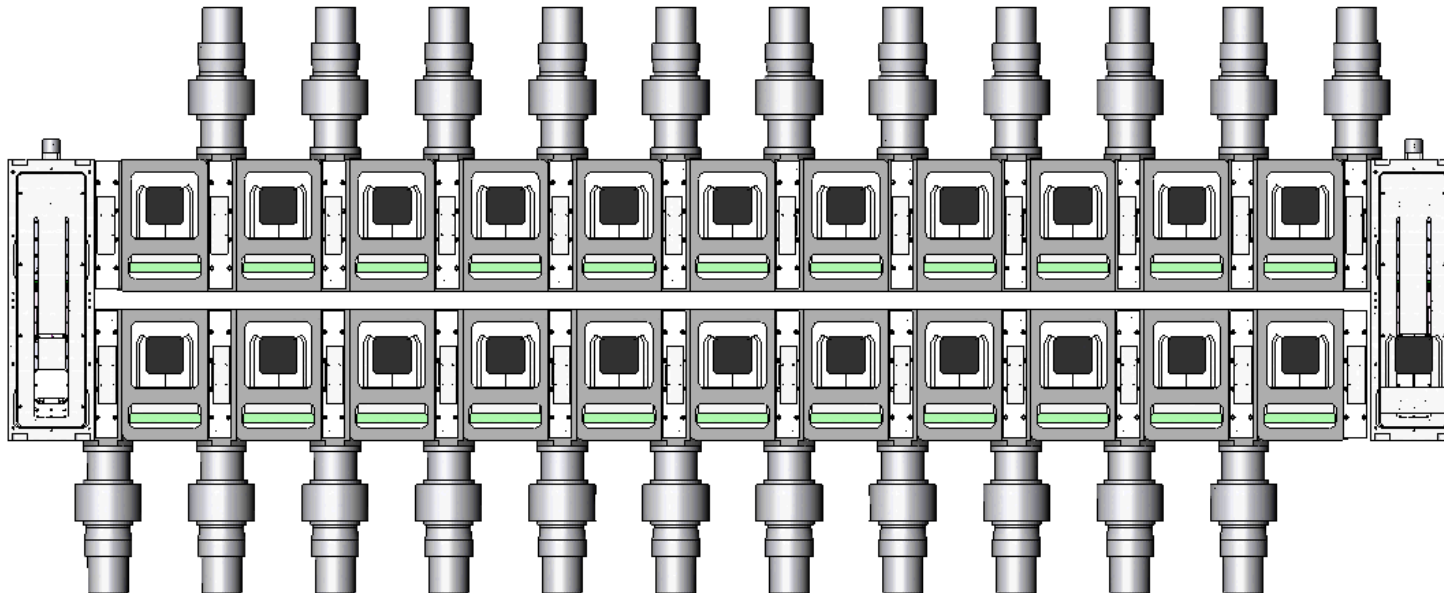
- Easily Add Process Stations
- Factory Efficient Small Footprint

❖ Low Cost of Ownership

- High Throughput
- High Utilization



HD Single Cell Processing Video

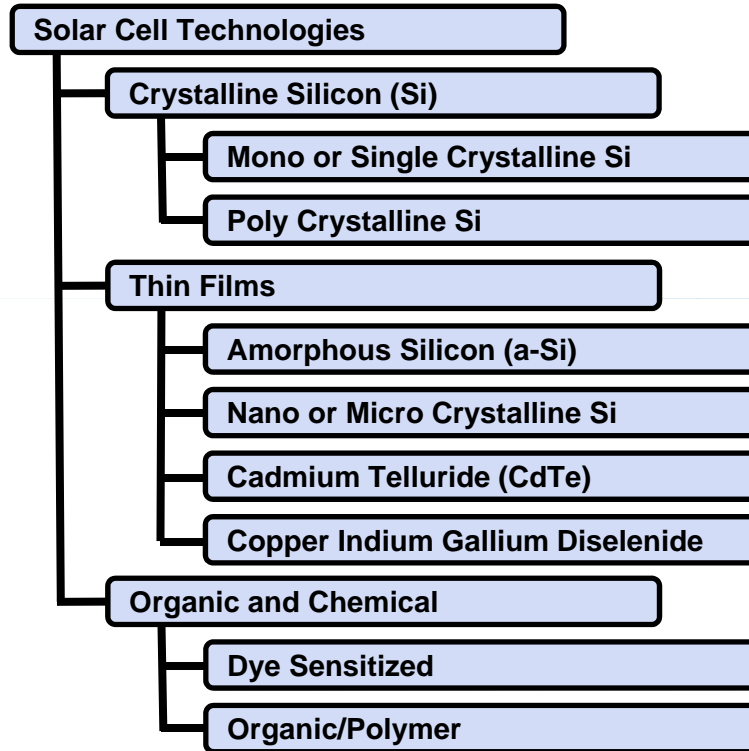


- **High Throughput, Individual Cell Processing**
- **Tight Process Control for Uniform Morphology**
- **High Capital Equipment Utilization**



Comparison of Solar Technologies

❖ Family of Solar Cells for Terrestrial Applications



Module Efficiency*	Record Lab Efficiency**	Efficiency Difference
15 – 18%	25%	39%
13 – 16%	20%	25%
5 – 8%	9.5%	10%
8 – 9%	10.1%	12%
8 – 10%	16.7%	67%
8 – 10%	19.9%	100%
N/A	10.4	N/A
N/A	5.1	N/A

CIGS Provides the Best Opportunity to Improve Module Efficiency (Lab vs. Production Headroom) and the Best Overall Thin Film Efficiency

* Acquired from Published Data/Sell Sheets

** Green MA, Emery K, Hishikawa Y, and Warta W. Solar Cell Efficiency Tables (Version 33). *Progress in Photovoltaics: Research and Applications* 2008; 17: 85-94.



Why CIGS? Demonstrated Attributes

- ❖ **High Efficiency** → Highest of the Thin Films and Equivalent to Poly Crystalline Si (Laboratory Scale)
- ❖ **Tolerant Chemistry** → Good Performance Achieved with a Wide Range of Cu/(In+Ga) and Ga/(In +Ga) Composition Ratios
- ❖ **Thin-Film Nature** → CIGS absorber is ~2.5 um compared to ~170 to 250 um for Si
 - CIGS Less Susceptible to Commodity Pricing of Raw Materials or to Material Shortages
- ❖ **Stability** → CIGS Does **NOT** Exhibit Light-Induced Instability Found with Some Thin-Film Solar Devices
- ❖ **Manufacturing Technology Advancements** → CIGS Benefits from the Manufacturing Technology and Equipment Developed in other Thin Film Arenas
 - Hard Disk Drive, Flat Panel Display, Architectural Plate Glass

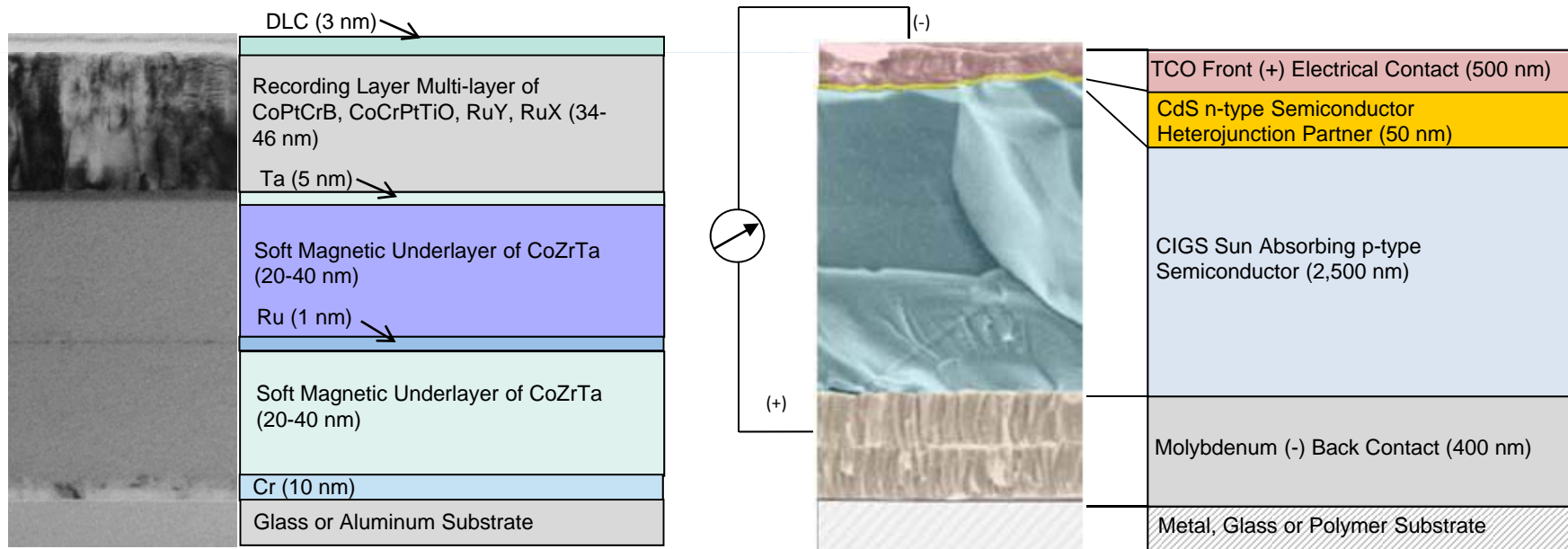


Hard Disk vs. CIGS Structure

❖ HD Structure is a Similar Multi-Layer Stack as CIGS

- **The CIGS Structure is About 20X Thicker than an HD Structure**

- ✓ HD Equipment Provides Precise Control of Very Thin Layers
- ✓ Question: **CAN** HD Equipment Provide High Volume Production Throughput of the Much Thicker CIGS Layers

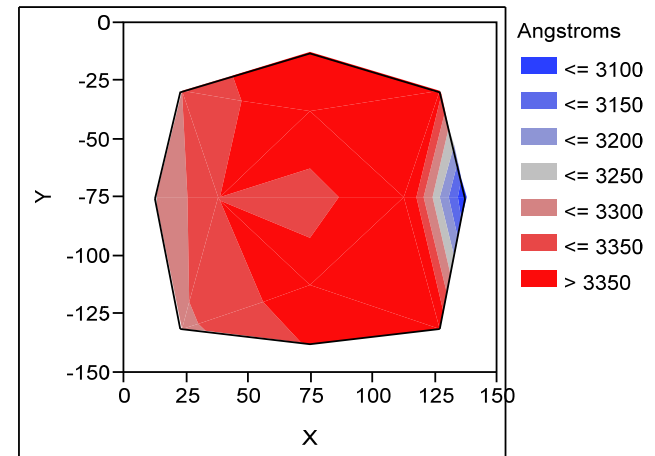
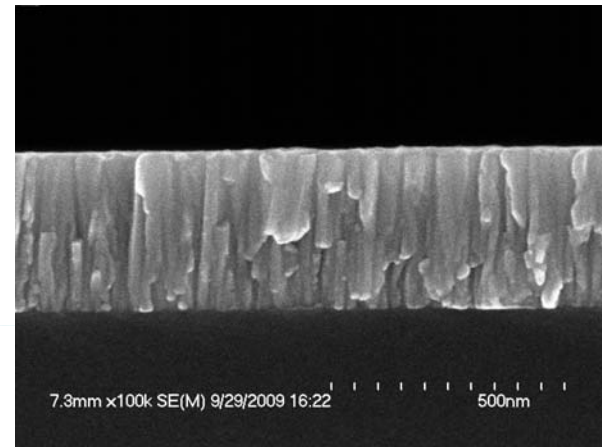


- **Preliminary Results → Yes**



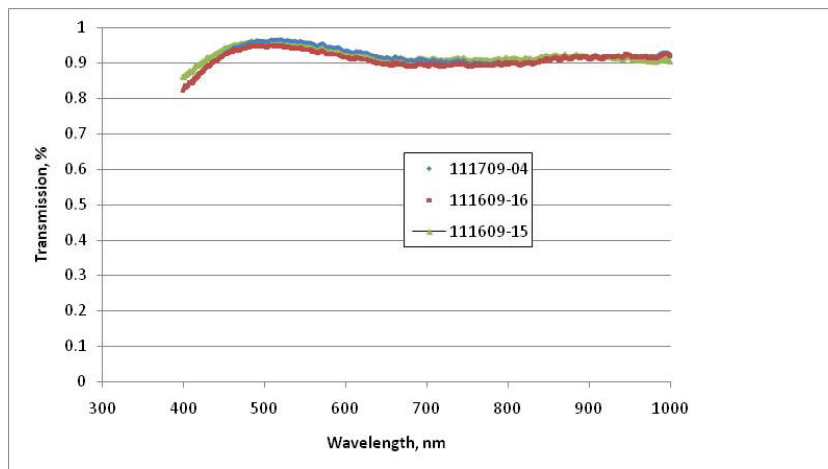
Current Results – Molybdenum Back Contact

- ❖ ***Demonstrated Back Contact Sputtering at High Throughput Rates Similar to HD***
- ❖ **Deposited In Sequential Fashion in 4 Separate Stations**
 - 4 sec Dwell Time Per Station
 - Results in ~17,000 Cells/Day
 - ✓ ~35kW/Day
 - Rate 35 nm/s-kW
 - Uniformity ~+/- 3%
 - Demonstrated >10% Efficiency CIGS Cells on High Rate Sputtered Mo



Current Results – TCO Front Contact

- ❖ ***Demonstrated TCO Sputtering at High Throughput Rates Similar to HD***
 - **Transmission (500-1000nm) > 90%**
 - **Resistance < 10 - 15 ohms/square**
 - **Rate up to 50 Ang/kW-sec**
 - **Dwell Time of 2.5 sec/station (4 Stations)**
 - **Crystalline Structure At Room Temperature**





Conclusions

- ❖ **Technology Development Progressing According to Schedule**
- ❖ **Initial Results Demonstrated that the HDD Equipment Can be Adapted for High Throughput Production of the CIGS Layers**
 - **Tools Are Capable of Meeting The ~13 MW/year Objective**
 - ✓ **Substrate Every 4-5 Seconds**
- ❖ **Molybdenum and Transparent Conductive Oxide Nearly Complete and Require Minor Optimization**
- ❖ **Metal Source Preliminary Evaporation Results Are Encouraging**



XsunX Approach → Low Risk, Speed to Market, Economically Viable

- ❖ **Small Area Wafers** → Similar to Techniques Successfully Employed in Laboratories
 - Smaller areas, about 5” squares, provide controlled deposition zones and improve solar cell performance by statistically reducing process variation and defects.
- ❖ **Technological Experience** → XsunX Staff has Previously Developed CIGS Evaporation Technology and Front and Back Contact Sputtering Used in Commercial Production
- ❖ **Not New Science** → Better Engineering, Processing Methods, and Use of Well Known Science
- ❖ **HD Operation Know-How** → High Factory Throughput and Yield, Low Down Time and Mean Time Between Failure, Low Capital Costs

Result: Revolutionizing the Thin Film Solar Cell Manufacturing Industry





Thank You!!



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